

ABSTRACT

[0038] The present invention comprises an integrated circuit fabricated on a single substrate where the integrated circuit comprises a first block comprising an enhancement mode pHEMT transistor on a substrate; a second block comprising a depletion mode pHEMT transistor on the substrate, the second block operatively connected to the first block; and a third block comprising a power pHEMT transistor on the substrate, the third block operatively connected to at least one of the first block and the second block. It is emphasized that this abstract is provided to comply with the rules requiring an abstract which will allow a searcher or other reader to quickly ascertain the subject matter of the technical disclosure. It is submitted with the understanding that it will not be used to interpret or limit the scope of meaning of the claims.